



# LA6586T

— Monolithic Linear IC  
**BTL Driver Single-Phase Full-Wave  
 Fan Motor Driver**

## Overview

The LA6586T is Single-phase bipolar fan motor is put into silent driving by means of BTL output linear drive, offering high efficiency and power saving by suppressing the reactive current. Lock protection and rotation signal (FG, RD) circuits are built in, ensuring optimum application to small fans for notebook PC, consumer equipment power supply, car audio system, CPU cooler, etc. that require high reliability and low noise.

## Functions

- Single-phase full-wave linear drive by BTL output (gain resistance 1k $\Omega$ -360k $\Omega$ , 51dB)
- Low-voltage operation possible, with wide operating voltage range (2.2 to 14.0V)
- Low saturation output (Upper + lower saturation voltage : Vosat (total)=1.2Vtyp, IO=200mA)
- Built-in lock protection and automatic reset circuits
- Built-in FG&RD outputs
- Built-in Hall bias (VHB=1.3V)
- Thermal protection circuit
- Extra-small package (MSOP10)

## Specifications

**Absolute Maximum Ratings** at Ta = 25 °C

Parameter	Symbol	Conditions	Ratings	Unit
Output voltage	V <sub>CC</sub> max		15	V
Allowable power dissipation	Pd max	Mounted on a specified board*	400	mW
Output current	I <sub>OUT</sub> max		0.6	A
Output withstand voltage	V <sub>OUT</sub> max		15	V
RD/FG output pin output withstand voltage	VRD/FG max		15	V
RD/FG output current	IRD/FG max		10	mA
HB output current	IB max		10	mA
Operating temperature	T <sub>opr</sub>		-30 to +90	°C
Storage temperature	T <sub>stg</sub>		-55 to +150	°C

\*Mounted on a specified board (114.3×76.2×1.5mm, Glass epoxy)

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## Recommended Operating Range at Ta = 25 °C

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V <sub>CC</sub>		2.2 to 14.0	V
Common-phase input voltage range of Hall input	V <sub>ICM</sub>		0 to V <sub>CC</sub> -1.5	V

## Electrical Characteristics at Ta = 25 °C, V<sub>CC</sub> = 5 V

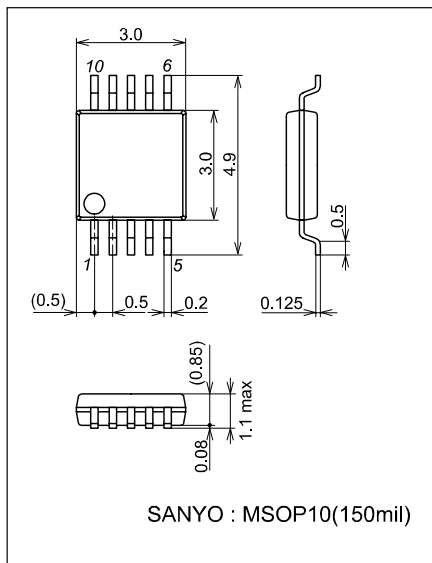
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Circuit current	I <sub>CC1</sub>	During drive (CT = L)	3	6	9	mA
	I <sub>CC2</sub>	During lock protection (CT = H)	2.5	5	7.5	mA
Lock detection capacitor charge current	I <sub>CT1</sub>		0.9	1.2	1.5	μA
Capacitor discharge current	I <sub>CT2</sub>		0.10	0.18	0.25	μA
Capacitor charge and discharge current ratio	R <sub>CT</sub>	R <sub>CD</sub> = I <sub>CT1</sub> /I <sub>CT2</sub>	5	6.5	8	-
CT charge voltage	V <sub>CT1</sub>		1.3	1.5	1.7	V
CT discharge voltage	V <sub>CT2</sub>		0.3	0.5	0.7	V
OUT output L saturation voltage	V <sub>OL</sub>	I <sub>O</sub> = 200 mA		0.25	0.45	V
OUT output H saturation voltage	V <sub>OH</sub>	I <sub>O</sub> = 200 mA		0.95	1.2	V
Input offset voltage	V <sub>OFST</sub>			3	6	mV
Hall input sensitivity	V <sub>HN</sub>	Zero peak value (including offset and hysteresis)		7	15	mV
Hall bias output L voltage	V <sub>HB</sub>	I <sub>HB</sub> = 5 mA	1.3	1.5	1.7	V
RD/FG input pin L voltage	V <sub>FG</sub>	I <sub>RD/FG</sub> = 5 mA		0.15	0.3	V
RD/FG input pin leak current	I <sub>FGL</sub>	V <sub>RD/FG</sub> = 15 V		1	30	μA
Overheat protection circuit	T <sub>SD</sub>	(*1) Designed target value	150	180	210	°C

(\*1) The standard is a design target and the measurement with a single unit is not made.

## Package Dimensions

unit : mm

3297

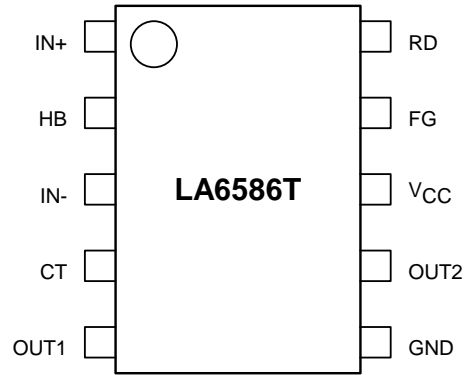


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## Truth Table

IN-	IN+	CT	OUT1	OUT2	FG	RD	Mode
H	L	L	H	L	L	L	During rotation
L	H		L	H	H		
-	-	H	OFF	OFF	-	H	During overheat protection

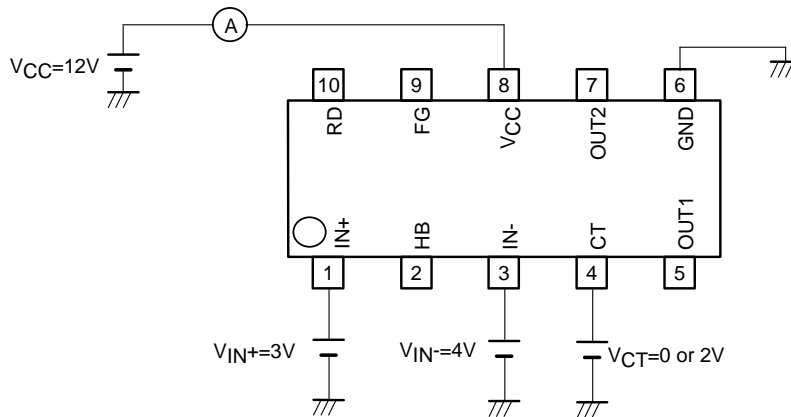
## Pin Assignment



Top view

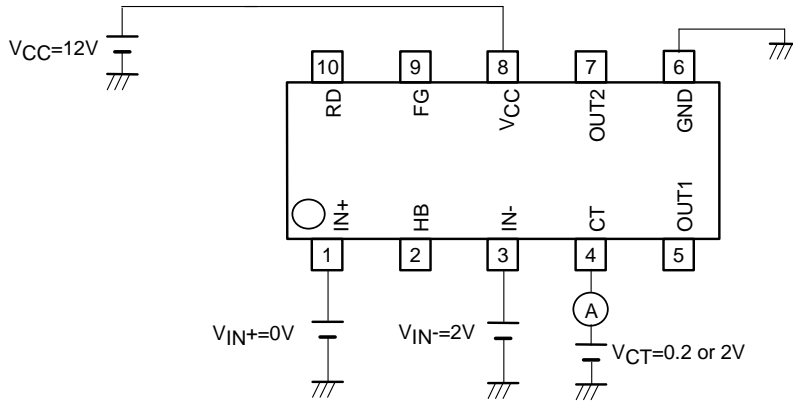
## Test Circuit Diagram

Input current ( $I_{CC}$ )

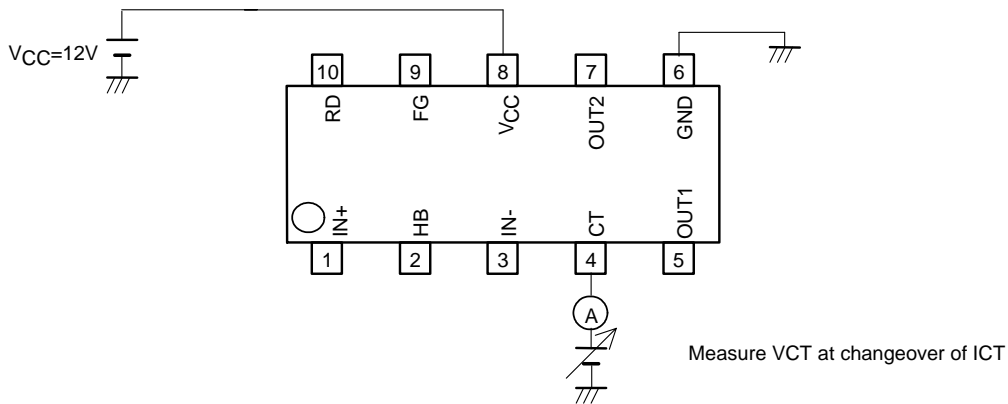


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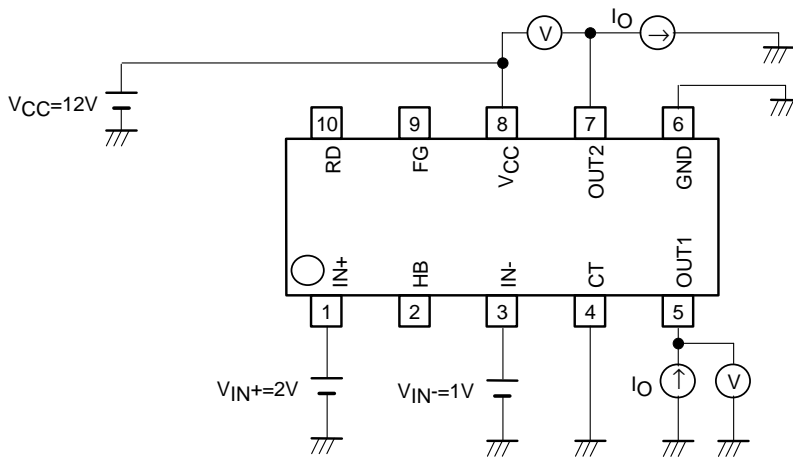
CT pin charge/discharge current ( $I_{CT}$ )



CT pin charge/discharge voltage (VCT)

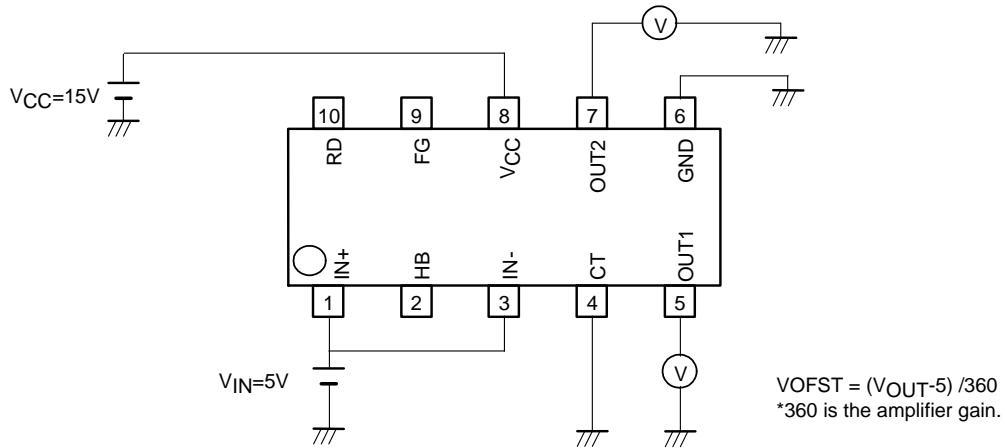


OUT output saturation voltage ( $V_{OL}$ ,  $V_{OH}$ )

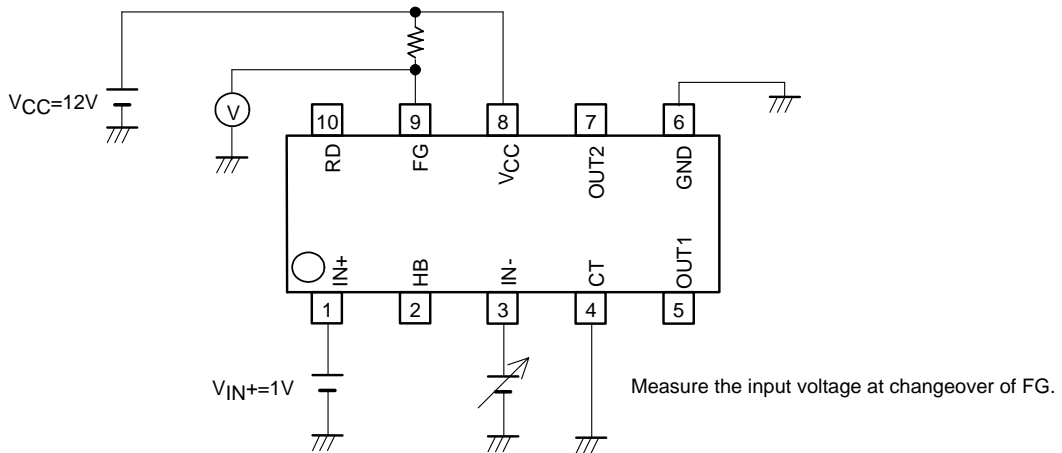


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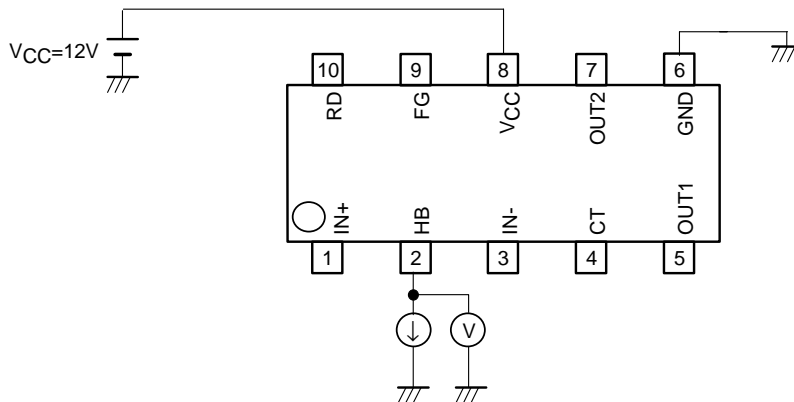
## Input offset voltage (VOFST)



## Hall input sensitivity (VHN)

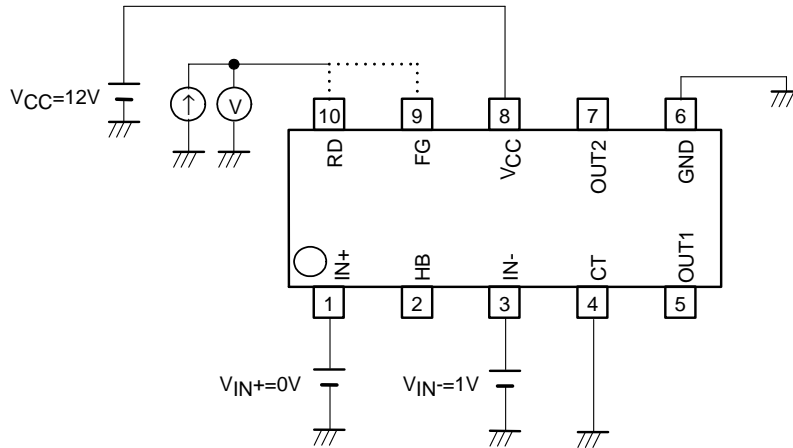


## Hall bias output voltage (VHB)

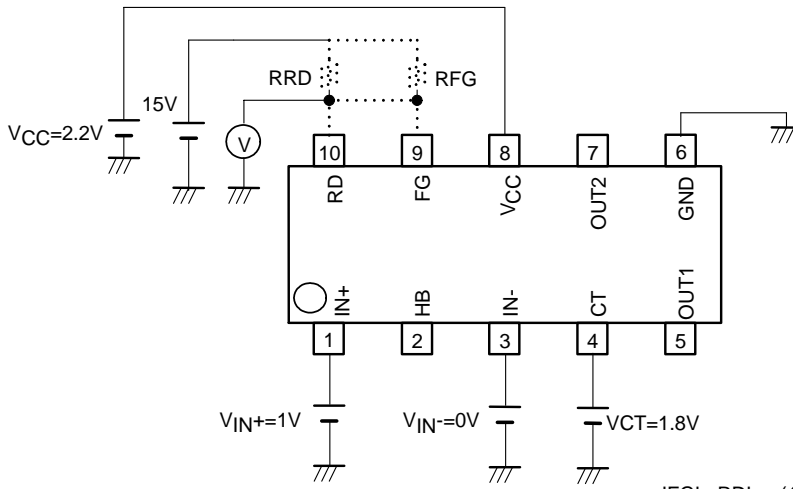


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FG, RD input pin L voltage (VFG, RD)

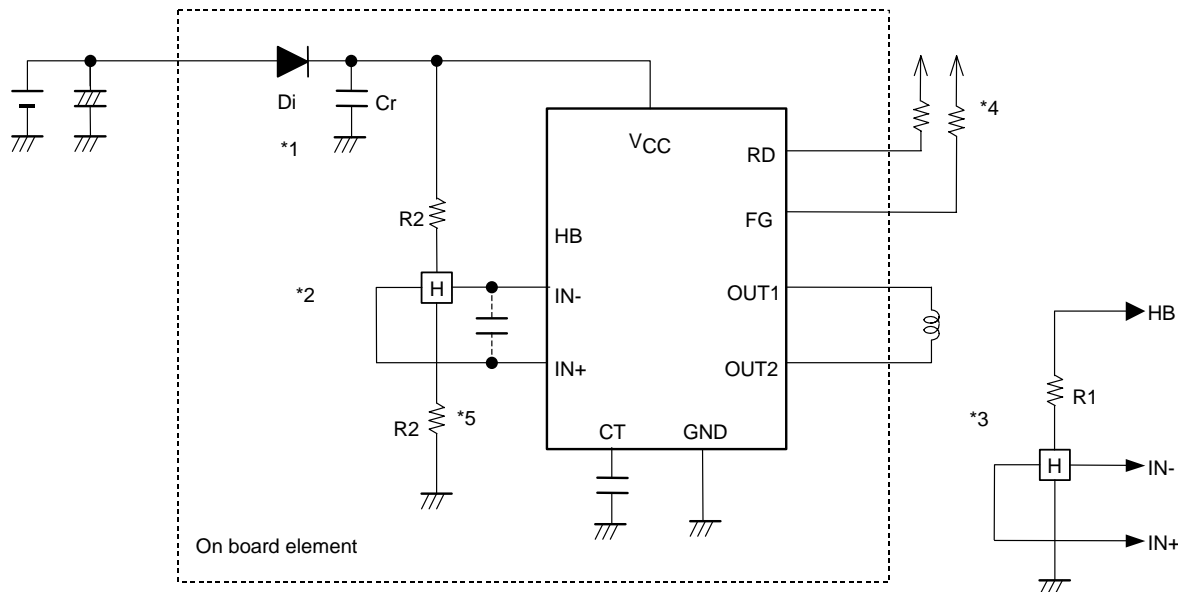


FG, RD input pin leakage current (IFGL, RDL)



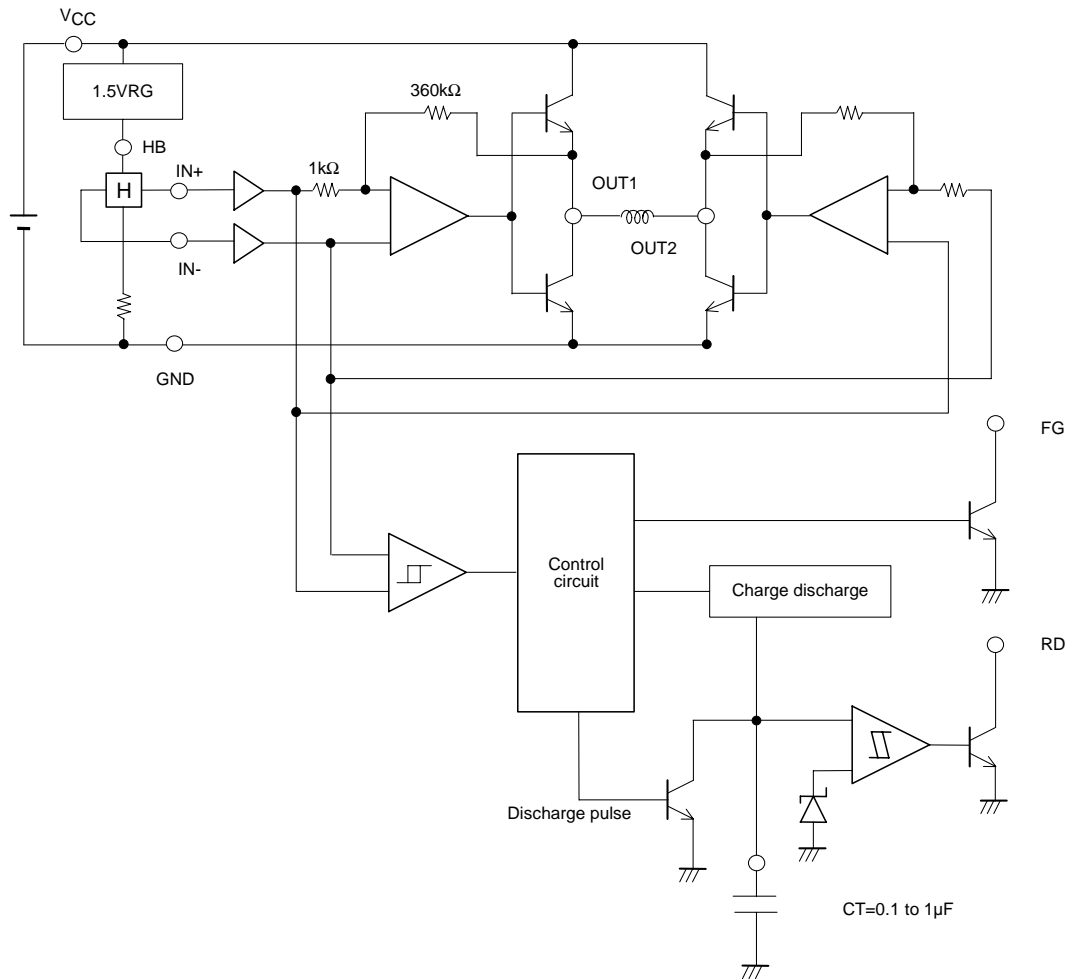
$$IFGL, RDL = (15 - V_{FG, RD}) / R_{RD, FG}$$

Sample Application Circuit



- \*1 To enhance the reliability, it is necessary to insert a capacitor Cr to secure the regenerative current route.
- \*2 To obtain Hall bias from V<sub>CC</sub>, carry out 1/2×V<sub>CC</sub> bias as shown in the figure. Linear driving is made through voltage control of the coil by amplifying the Hall output. When the Hall element output is large, the startup performance and efficiency are improved. Adjustment of the Hall element can reduce the noise further.
- \*3 To obtain Hall bias from the HB pin, carry out constant-voltage bias at about 1.5 V. which enables the Hall element to generate the stable Hall output satisfactory in temperature characteristics. The Hall output amplitude is adjusted with R1. (In the case of V<sub>CC</sub> = 12 V, \*2 proves advantageous in terms of heat generation in IC.) This applies to the case of MFP-10S.
- \*4 Keep this open when not used.
- \*5 When the wiring from the Hall output to IC Hall input is long, noise may be carried through the wiring. In this case, insert the capacitor as shown in the figure.

Internal Equivalent Circuit



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